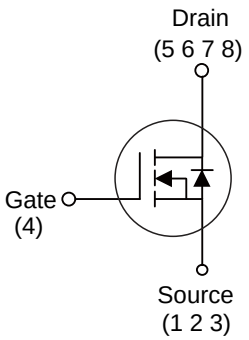
■ PRODUCT CHARACTERISTICS

V_{DSS}	60V
$R_{DS(ON)}$ Typ(@V_{GS}=10V)	15mΩ
$R_{DS(ON)}$ Typ(@V_{GS}=4.5V)	20mΩ
I_D	35A

Symbol

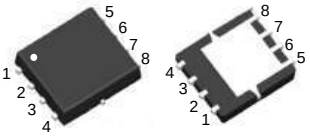


■ APPLICATIONS

* Motor Control
* High Performance SMPS
* DC/DC Coverter

■ FEATURE

* Low Gate Charge
* Ultra-low RDS(ON)



PDFN5X6

■ ORDER INFORMATION

Order Codes		Package	Packing
Halogen-Free	Halogen		
N/A	MOT6522G	PDFN5X6	5000 pieces/Reel

■ ABSOLUTE MAXIMUM RATINGS(T_A=25°C,unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DSS}	60	V
Gate-Source Voltage	V_{GSS}	±20	V
Drain Current Continuous(@V_{GS}=10V ,T_A=25°C)	I_D	35	A
Drain Current Pulsed	I_{DM}	140	A
Avalanche Energy *	E_{AS}	64	mJ
Power Dissipation	P_D	42	W
Junction Temperature	T_J	+150	°C
Storage Temperature	T_{STG}	-55~ +150	°C

■ THERMAL CHARACTERISTICS

Parameter	Symbol	Typ	Unit
Junction to Case	R_{thJC}	3	°C/W

Note: * EAS condition: T_J=25°C ,V_{DD}=30V ,V_G=10V ,L=0.5mH,R_g=25Ω

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Off characteristics						
Drain to Source Breakdown Voltage	V_{DSS}	V_{GS}=0V,I_D=250μA	60	-	-	V
Drain to Source Leakage Current	I_{DSS}	V_{DS}=60V,V_{GS}=0V	-	-	1	μA
Gate to Source Forward Leakage	$I_{GSS(F)}$	V_{DS}=0V, V_{GS}=+20V	-	-	100	nA
Gate to Source Reverse Leakage	$I_{GSS(R)}$	V_{DS}=0V, V_{GS}=-20V	-	-	-100	nA
On characteristics						
Drain to Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V,I_D=20A	-	15	20	mΩ
		V_{GS}=4.5V,I_D=20A	-	20	25	mΩ
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS}=V_{GS},I_D=250μA	1	1.9	2.5	V
Dynamic characteristics						
Gate Resistance	R_g	V_{GS}=0V,V_{DS}=0V ,f=1.0MHz	-	2.8	-	Ω
Forward Transconductance	g_{fs}	V_{DS}=10V,I_D=3A	-	7	-	S
Input Capacitance	C_{iss}	V_{DS}=20V,V_{GS}=0V f=1.0MHz	-	612	-	pF
Output Capacitance	C_{oss}		-	271	-	pF
Reverse Transfer Capacitance	C_{rss}		-	20	-	pF
Resistive Switching Characteristics						
Turn-on Delay Time	$t_{d(ON)}$	I_D=30A, V_{DS}=30V R_G=1.8Ω ,V_{GS}=10V	-	11	-	ns
Rise Time	t_r		-	79	-	ns
Turn-off Delay Time	$t_{d(OFF)}$		-	33	-	ns
Fall Time	t_f		-	107	-	ns
Total Gate Charge	Q_g	I_D=30A, V_{DS}=30V V_{GS}=10V	-	45	-	nC
Gate to Source Charge	Q_{gs}		-	8	-	nC
Gate to Drain("Miller") Charge	Q_{gd}		-	11	-	nC
Source-Drain Diode Characteristics						
Continuous Source Current(Body Diode)	I_S		-	-	35	A
Maximum Pulsed Current(Body Diode)	I_{SM}		-	-	140	A
Diode Forward Voltage	V_{SD}	I_{SD}=1A, V_{GS}=0V	-	0.74	1.2	V
Reverse Recovery Time	t_{rr}	I_{SD}=30 A, T_J=25 °C dI /dt=100A/μs	-	14	-	ns
Reverse Recovery Charge	Q_{rr}		-	10	-	nC

■ TYPICAL CHARACTERISTICS

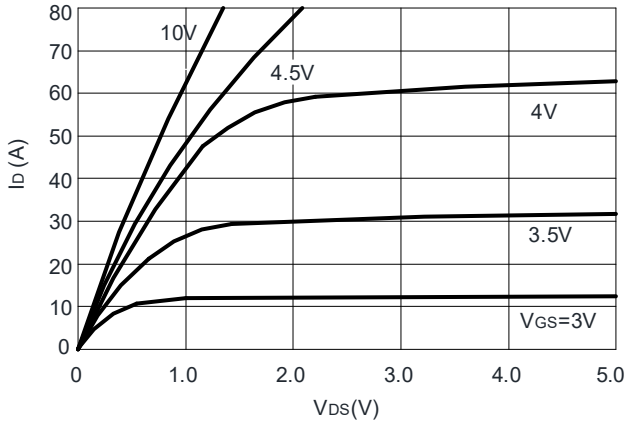


Figure 1: Output Characteristics

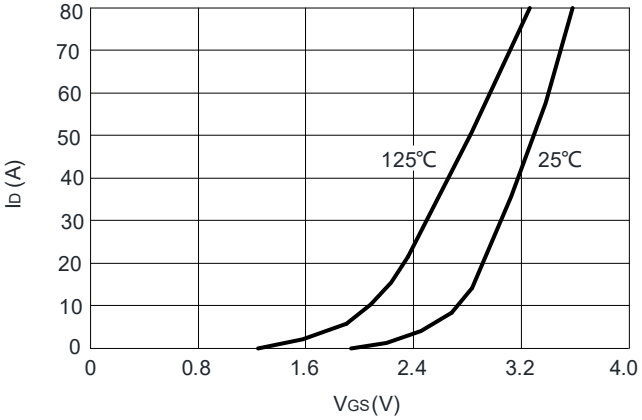


Figure 2:Typical Transfer Characteristics

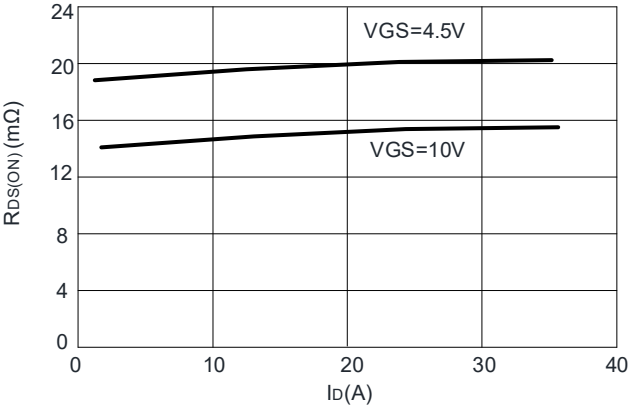


Figure 3: On-resistance vs. Drain Current

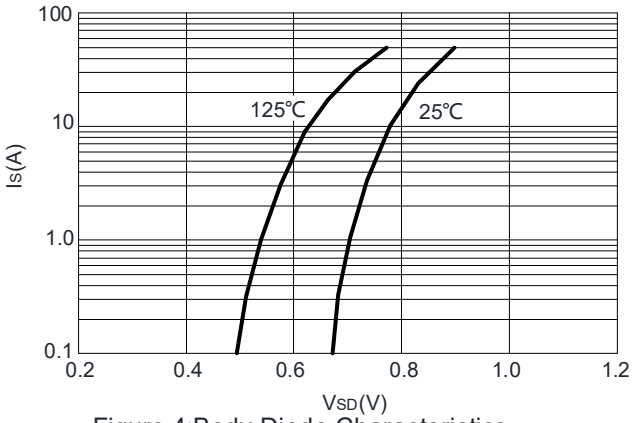


Figure 4:Body Diode Characteristics

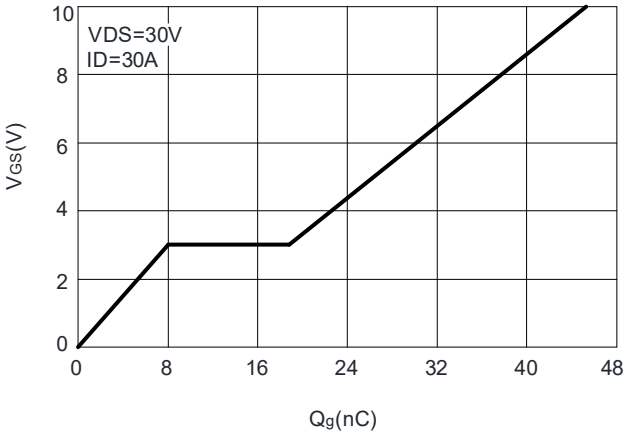


Figure 5: Gate Charge Characteristics

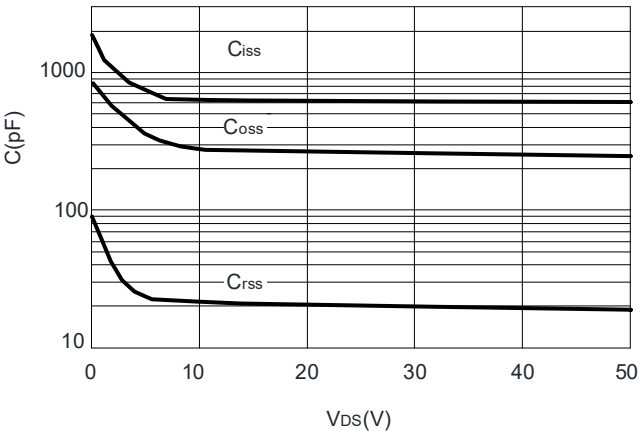


Figure 6:Capacitance Characteristics

■ TYPICAL CHARACTERISTICS(Cont.)

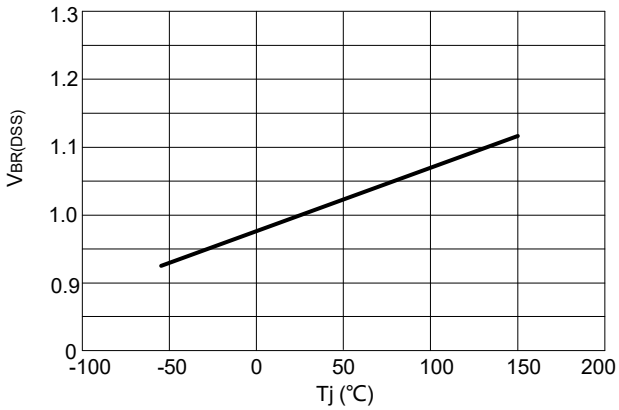


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

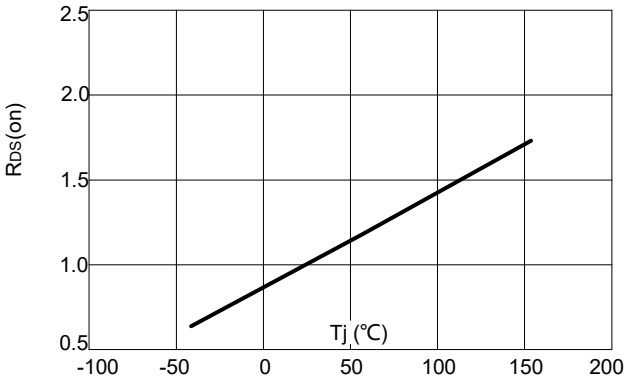


Figure 8: Normalized on Resistance vs. Junction Temperature

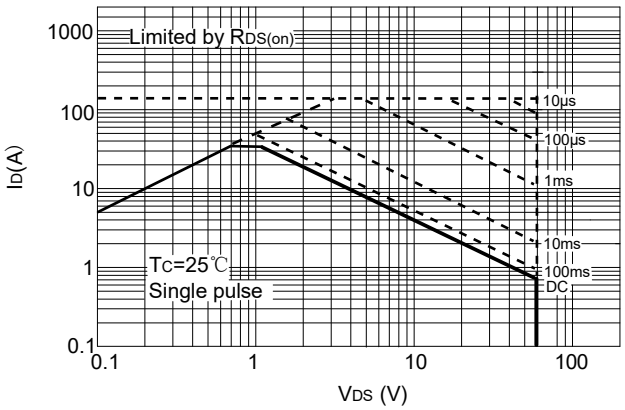


Figure 9: Maximum Safe Operating Area

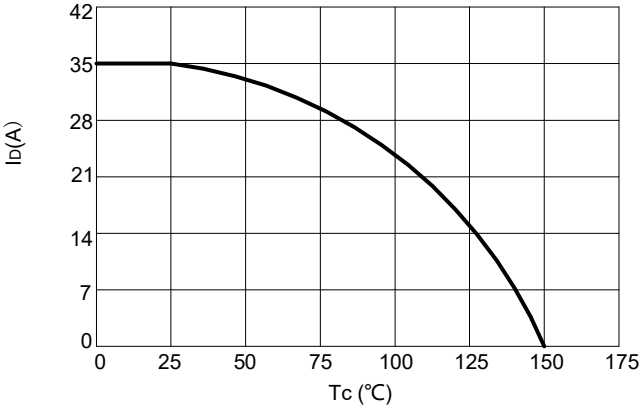
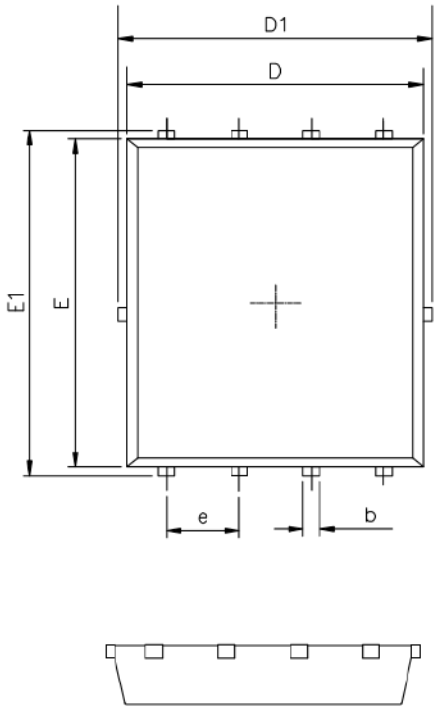
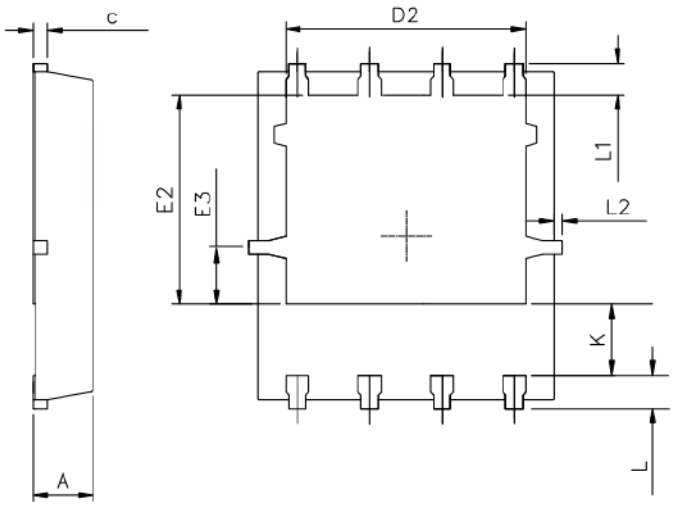


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

■ PDFN5X6 PACKAGE OUTLINE DIMENSIONS





UNIT:mm

	MIN	NOM	MAX
A	0.90	1.00	1.10
b	0.25	0.35	0.50
c	0.10	0.20	0.30
D	4.80	5.00	5.30
D1	4.90	5.10	5.50
D2	3.92	4.02	4.20
E	5.65	5.75	5.85
E1	5.90	6.05	6.20
E2	3.325	3.525	3.775
E3	0.80	0.90	1.00
e		1.27	
L	0.40	0.55	0.70
L1		0.65	
L2	0.00		0.15
K	1.00	1.30	1.50

RECOMMENDED LAND PATTERN